

#### **60V N-Channel Enhancement Mode MOSFET**

Voltage 60 V Current

18 A

#### **Features**

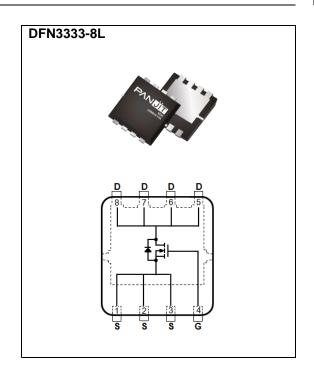
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@10A<34mΩ
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@5A<40m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	l <sub>D</sub>	18		
	Tc=100°C		12	А	
Pulsed Drain Current(Note 1)	Tc=25°C	I <sub>DM</sub>	72	<u> </u>	
Power Dissipation	Tc=25°C	Po	24	147	
	Tc=100°C		8	W	
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C	lο	5		
	T <sub>A</sub> =70°C		4	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	2	W	
	T <sub>A</sub> =70°C		1.3		
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		E <sub>AS</sub>	24	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	6.3	°C/W	
	Junction to Ambient	R <sub>θJA</sub>	62.5		

• Limited only By Maximum Junction Temperature



### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.83	2.5		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	28	34	mΩ	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	33	40	mtz	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic <sup>(Note 7)</sup>			_		_		
Total Gate Charge	$Q_g$	\/ 00\/ L 40A	-	20	-	nC	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =30V, I <sub>D</sub> =10A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	3.8	-		
Gate-Drain Charge	$Q_gd$	VGS=10 V(1000 1)2/	-	3.9	-		
Input Capacitance	Ciss	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	1173	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	63	-		
Reverse Transfer Capacitance	Crss	I=IIVIDZ	-	44	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/   40	-	7.1	-		
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =1A,	-	25	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =10V, R <sub>G</sub> =6 $\Omega$	-	31	-		
Turn-Off Fall Time	t <sub>f</sub>	(14010-1,2)	-	20	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	17	А	
Diode Forward Current	Is						
Reverse Recovery Time	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.72	1	V	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I<sub>AS</sub>=22A, V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, Starting T<sub>J</sub>=25°C.
- 7. Guaranteed by design, not subject to production testing.

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#### **TYPICAL CHARACTERISTIC CURVES**

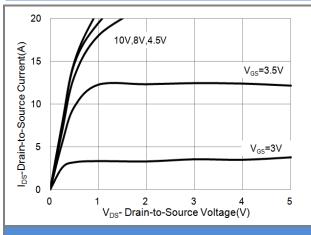
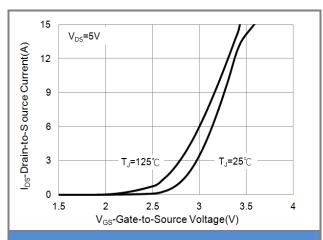


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

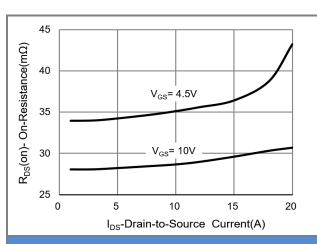


Fig.3 On-Resistance vs. Drain Current

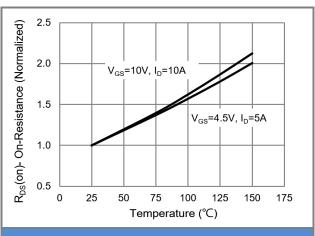
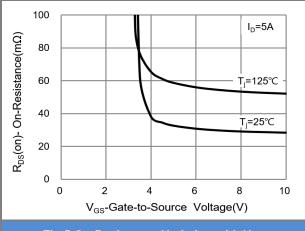


Fig.4 On-Resistance vs. Junction temperature





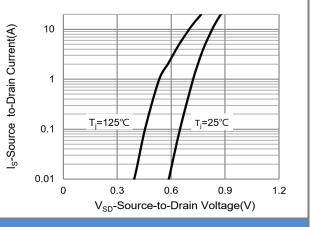


Fig.6 Source-Drain Diode Forward Voltage



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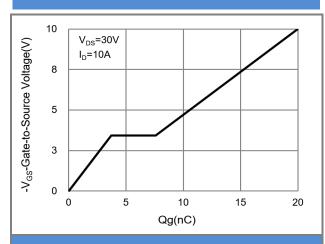


Fig.7 Gate-Charge Characteristics

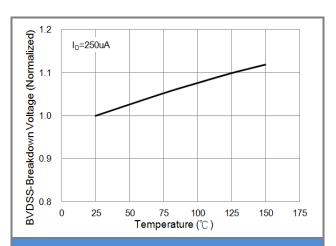


Fig.8 Breakdown Voltage Variation vs. Temperature

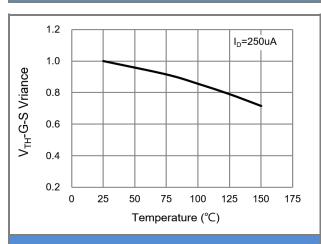


Fig.9 Threshold Voltage Variation with Temperature

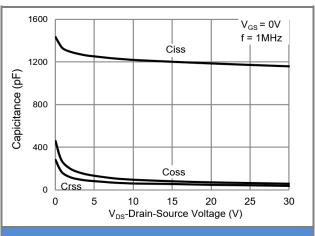
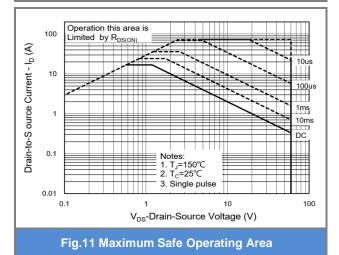


Fig.10 Capacitance vs. Drain-Source Voltage



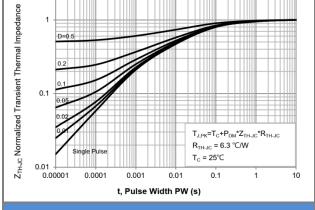


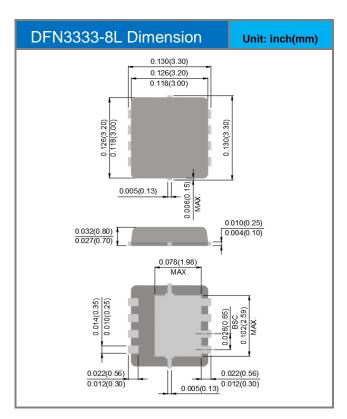
Fig.12 Normalized Transient Thermal Impedance

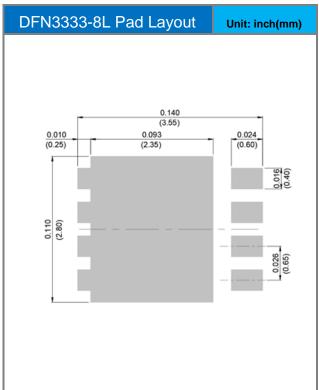


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4468AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4468	Halogen free RoHS compliant

### **Packaging Information & Mounting Pad Layout**





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